

## Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on) \text{ max}}$               | $I_D$<br>$T_C = +25^\circ\text{C}$ |
|---------------|----------------------------------------|------------------------------------|
| -40V          | 11m $\Omega$ @ $V_{GS} = -10\text{V}$  | -35A                               |
|               | 15m $\Omega$ @ $V_{GS} = -4.5\text{V}$ | -30A                               |

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

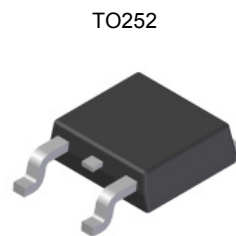
- DC-DC Converters
- Power management functions
- Backlighting

## Features and Benefits

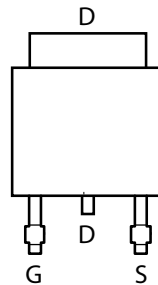
- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

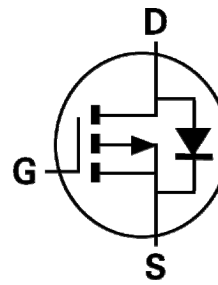
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (approximate)



Top View



Top View  
Pin-Out



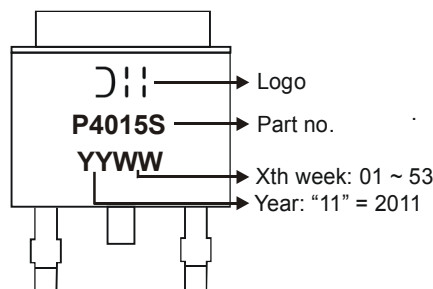
Equivalent Circuit

## Ordering Information (Note 4)

| Part Number    | Compliance | Case  | Packaging         |
|----------------|------------|-------|-------------------|
| DMP4015SK3-13  | Standard   | TO252 | 2,500/Tape & Reel |
| DMP4015SK3Q-13 | Automotive | TO252 | 2,500/Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

## Marking Information



**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                                 |                  |                                                        | Symbol    | Value      | Units |
|----------------------------------------------------------------|------------------|--------------------------------------------------------|-----------|------------|-------|
| Drain-Source Voltage                                           |                  |                                                        | $V_{DSS}$ | -40        | V     |
| Gate-Source Voltage                                            |                  |                                                        | $V_{GSS}$ | $\pm 25$   | V     |
| Continuous Drain Current (Note 5) $V_{GS} = -10\text{V}$       | Steady State     | $T_C = +25^\circ\text{C}$<br>$T_C = +70^\circ\text{C}$ | $I_D$     | -35<br>-27 | A     |
|                                                                | Steady State     | $T_A = +25^\circ\text{C}$<br>$T_A = +70^\circ\text{C}$ | $I_D$     | -14<br>-11 | A     |
| Continuous Drain Current (Note 5) $V_{GS} = -10\text{V}$       | $t < 10\text{s}$ | $T_A = +25^\circ\text{C}$<br>$T_A = +70^\circ\text{C}$ | $I_D$     | -22<br>-18 | A     |
| Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%) |                  |                                                        | $I_{DM}$  | -100       | A     |
| Maximum Body Diode Forward Current (Note 5)                    |                  |                                                        | $I_S$     | -5.5       | A     |
| Avalanche Current (Note 6)                                     |                  |                                                        | $I_{AS}$  | -57        | A     |
| Avalanche Energy (Note 6)                                      |                  |                                                        | $E_{AS}$  | 162        | mJ    |

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                   |                           | Symbol          | Value       | Units              |
|--------------------------------------------------|---------------------------|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 5)                 | $T_A = +25^\circ\text{C}$ | $P_D$           | 3.5         | W                  |
|                                                  | $T_A = +70^\circ\text{C}$ |                 | 2.2         |                    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady state              | $R_{\theta JA}$ | 36          | $^\circ\text{C/W}$ |
|                                                  | $t < 10\text{s}$          |                 | 15          |                    |
| Thermal Resistance, Junction to Case (Note 5)    | Steady state              | $R_{\theta JC}$ | 4.5         | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range          |                           | $T_J, T_{STG}$  | -55 to +150 | $^\circ\text{C}$   |

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                          | Symbol       | Min  | Typ   | Max       | Unit          | Test Condition                                                                     |
|-----------------------------------------|--------------|------|-------|-----------|---------------|------------------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 7)</b>     |              |      |       |           |               |                                                                                    |
| Drain-Source Breakdown Voltage          | $BV_{DSS}$   | -40  | —     | —         | V             | $V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$                                        |
| Zero Gate Voltage Drain Current         | $I_{DSS}$    | —    | —     | -1        | $\mu\text{A}$ | $V_{DS} = -40\text{V}, V_{GS} = 0\text{V}$                                         |
| Gate-Source Leakage                     | $I_{GSS}$    | —    | —     | $\pm 100$ | nA            | $V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$                                      |
| <b>ON CHARACTERISTICS (Note 7)</b>      |              |      |       |           |               |                                                                                    |
| Gate Threshold Voltage                  | $V_{GS(th)}$ | -1.5 | -2.0  | -2.5      | V             | $V_{DS} = V_{GS}, I_D = -250\mu\text{A}$                                           |
| Static Drain-Source On-Resistance       | $R_{DS(on)}$ | —    | 7     | 11        | m $\Omega$    | $V_{GS} = -10\text{V}, I_D = -9.8\text{A}$                                         |
|                                         |              | —    | 9     | 15        |               | $V_{GS} = -4.5\text{V}, I_D = -9.8\text{A}$                                        |
| Forward Transfer Admittance             | $ Y_{fs} $   | —    | 26    | —         | S             | $V_{DS} = -20\text{V}, I_D = -9.8\text{A}$                                         |
| Diode Forward Voltage                   | $V_{SD}$     | —    | -0.7  | -1.0      | V             | $V_{GS} = 0\text{V}, I_S = -1\text{A}$                                             |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b> |              |      |       |           |               |                                                                                    |
| Input Capacitance                       | $C_{iss}$    | —    | 4234  | —         | pF            | $V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$<br>$f = 1.0\text{MHz}$                  |
| Output Capacitance                      | $C_{oss}$    | —    | 1036  | —         |               |                                                                                    |
| Reverse Transfer Capacitance            | $C_{rss}$    | —    | 526   | —         |               |                                                                                    |
| Gate Resistance                         | $R_G$        | —    | 7.77  | —         | $\Omega$      | $V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$                        |
| Total Gate Charge                       | $Q_g$        | —    | 47.5  | —         | nC            | $V_{DS} = -20\text{V}, V_{GS} = -5\text{V}$<br>$I_D = -9.8\text{A}$                |
| Gate-Source Charge                      | $Q_{gs}$     | —    | 14.2  | —         |               |                                                                                    |
| Gate-Drain Charge                       | $Q_{gd}$     | —    | 13.5  | —         |               |                                                                                    |
| Turn-On Delay Time                      | $t_{D(on)}$  | —    | 13.2  | —         | ns            | $V_{GS} = -10\text{V}, V_{DD} = -20\text{V},$<br>$R_G = 6\Omega, I_D = -1\text{A}$ |
| Turn-On Rise Time                       | $t_r$        | —    | 10.0  | —         |               |                                                                                    |
| Turn-Off Delay Time                     | $t_{D(off)}$ | —    | 302.7 | —         |               |                                                                                    |
| Turn-Off Fall Time                      | $t_f$        | —    | 137.9 | —         |               |                                                                                    |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - UIS in production with  $L = 0.1\text{mH}$ ,  $T_J = +25^\circ\text{C}$ .
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

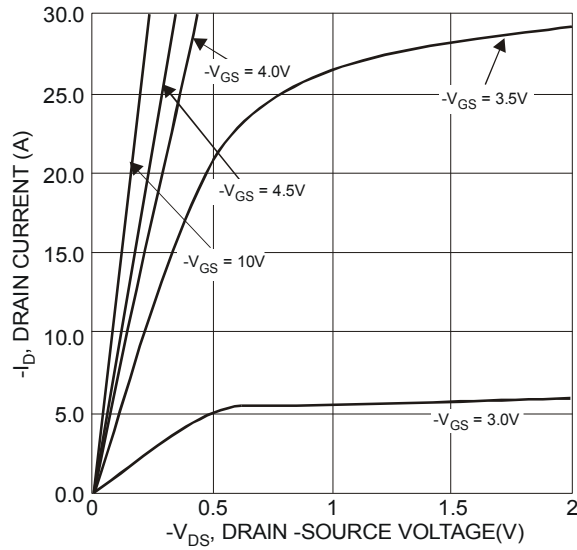


Fig. 1 Typical Output Characteristics

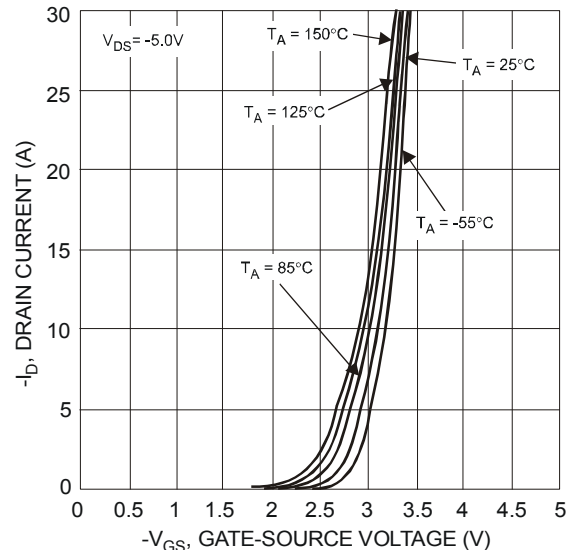


Fig. 2 Typical Transfer Characteristics

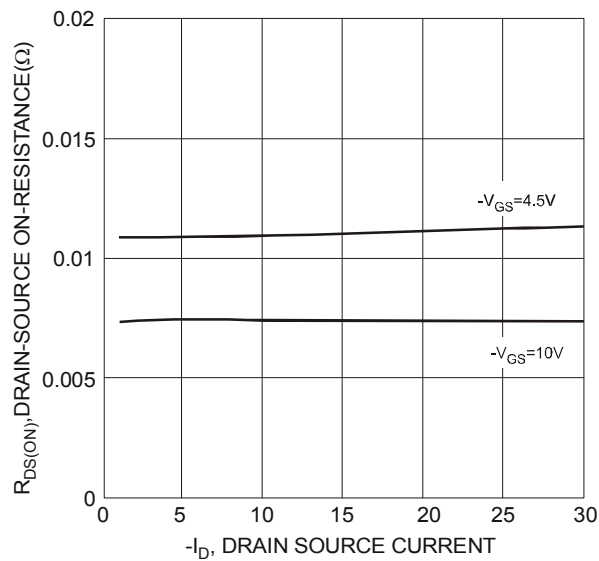


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

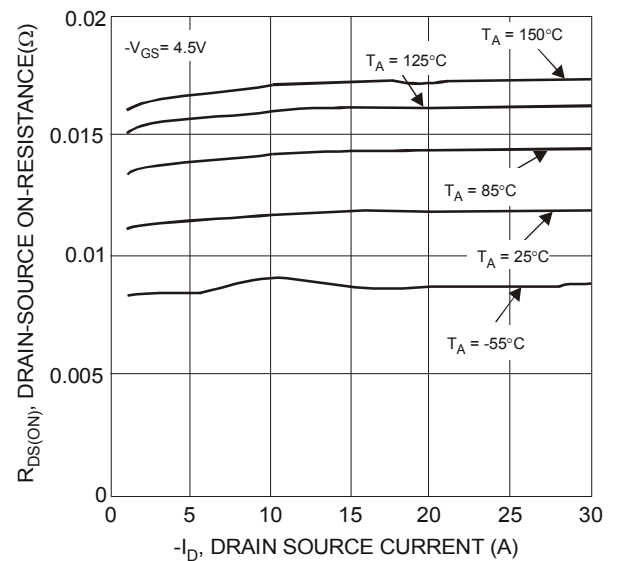


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

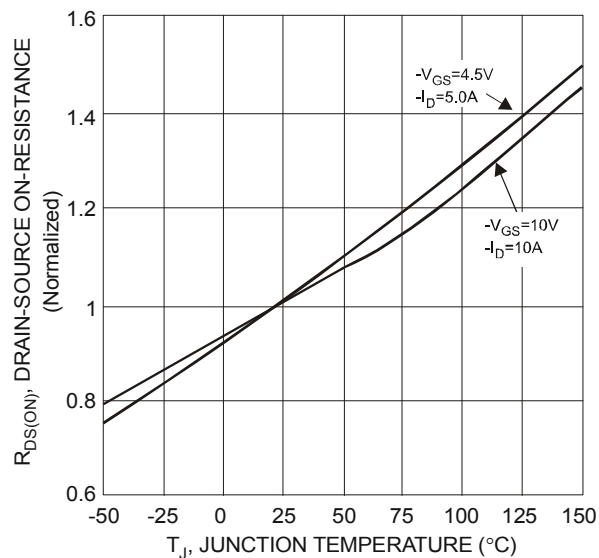


Fig. 5 On-Resistance Variation with Temperature

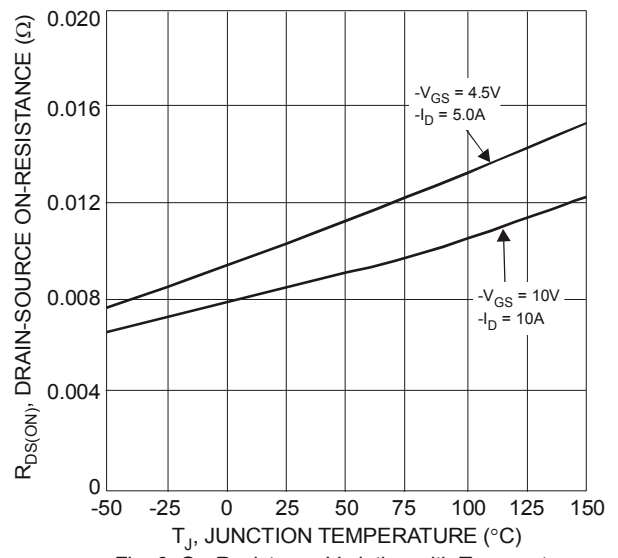


Fig. 6 On-Resistance Variation with Temperature

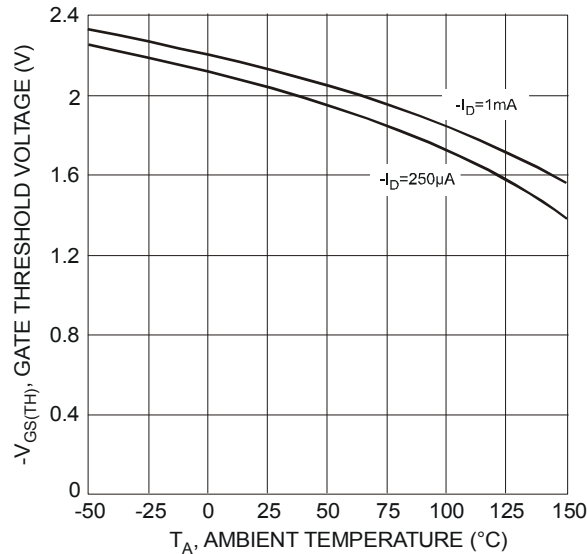


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

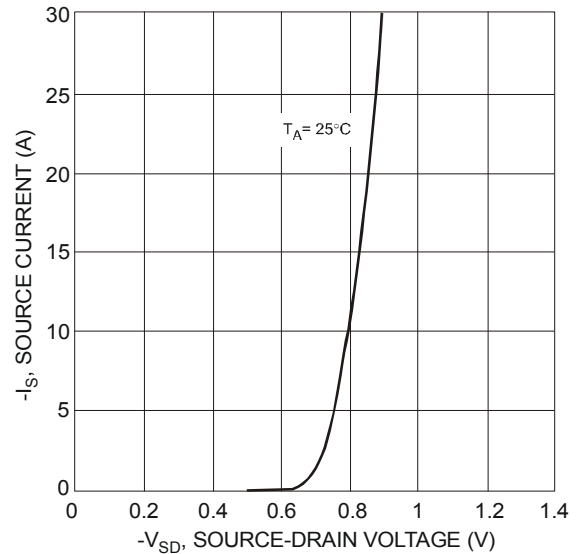


Fig. 8 Diode Forward Voltage vs. Current

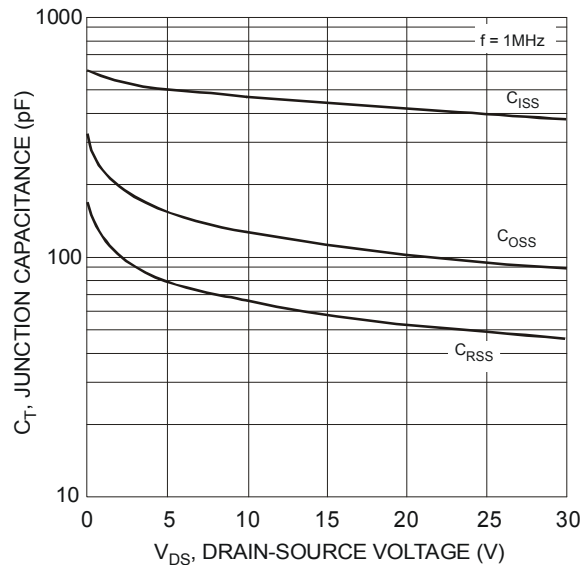


Fig. 9 Typical Junction Capacitance

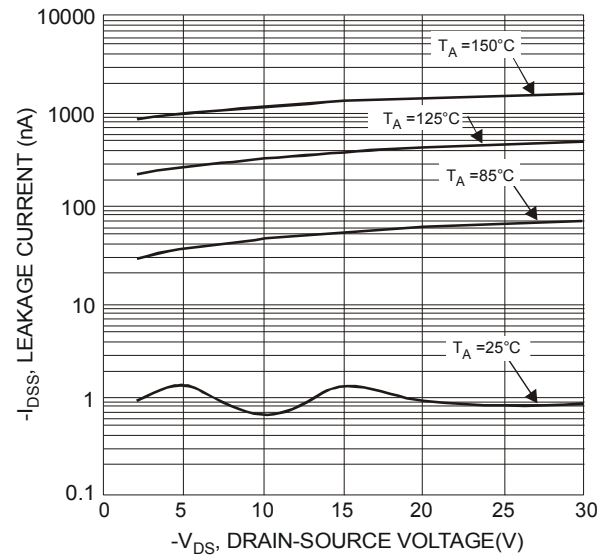


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

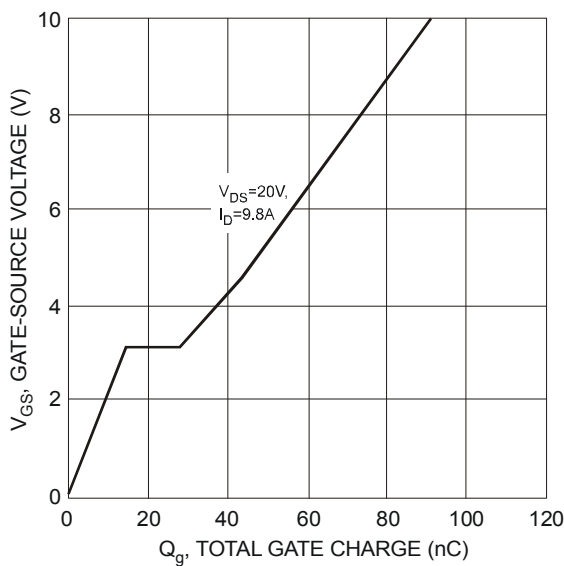


Fig. 11 Gate-Charge Characteristics

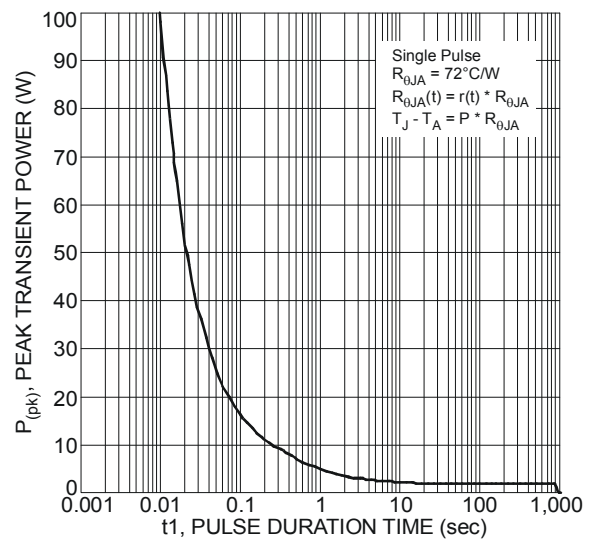


Fig. 12 Single Pulse Maximum Power Dissipation

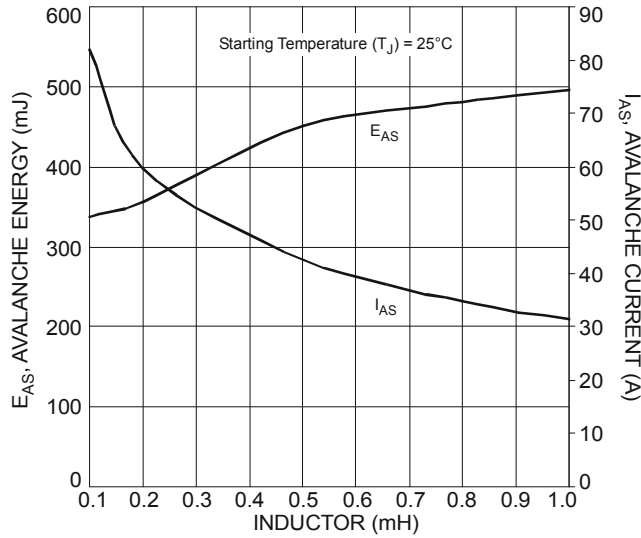


Fig. 13 Single-Pulse Avalanche Tested

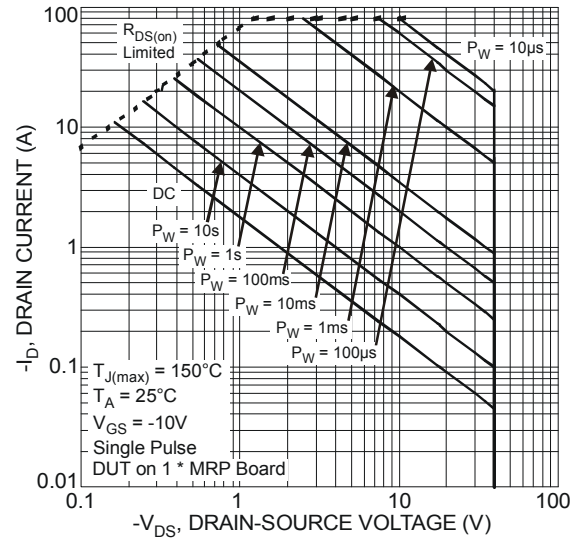


Fig. 14 SOA, Safe Operation Area

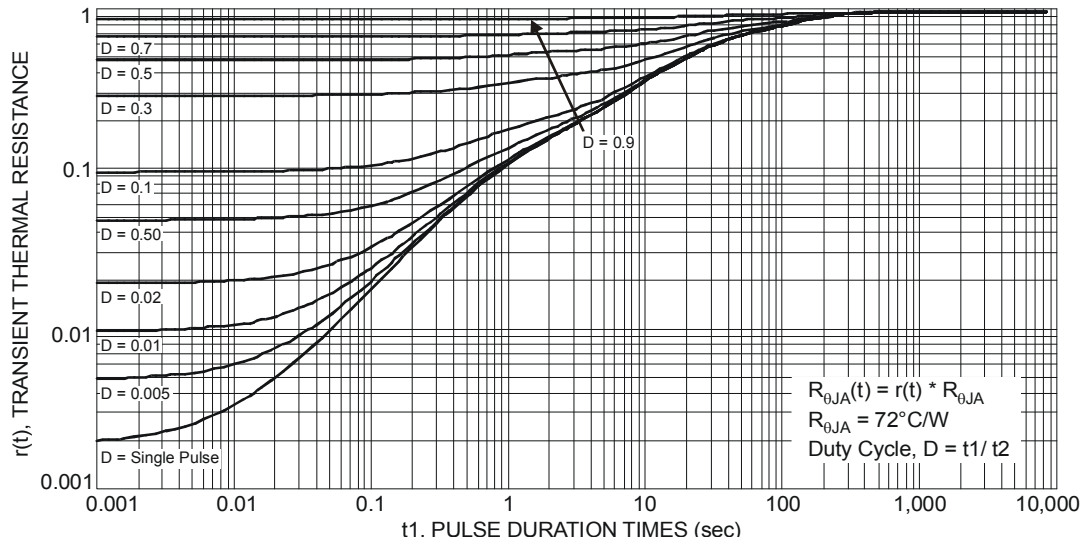
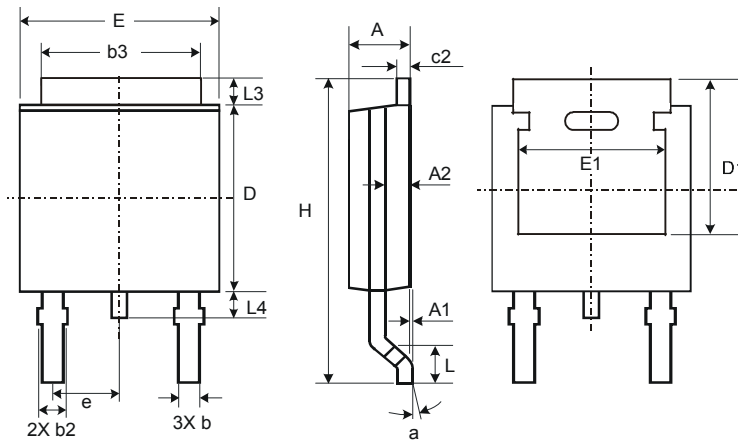


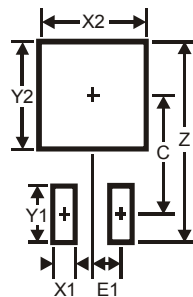
Fig. 15 Transient Thermal Resistance

## Package Outline Dimensions



| TO252                |      |       |       |
|----------------------|------|-------|-------|
| Dim                  | Min  | Max   | Typ   |
| A                    | 2.19 | 2.39  | 2.29  |
| A1                   | 0.00 | 0.13  | 0.08  |
| A2                   | 0.97 | 1.17  | 1.07  |
| b                    | 0.64 | 0.88  | 0.783 |
| b2                   | 0.76 | 1.14  | 0.95  |
| b3                   | 5.21 | 5.46  | 5.33  |
| c2                   | 0.45 | 0.58  | 0.531 |
| D                    | 6.00 | 6.20  | 6.10  |
| D1                   | 5.21 | —     | —     |
| e                    | —    | —     | 2.286 |
| E                    | 6.45 | 6.70  | 6.58  |
| E1                   | 4.32 | —     | —     |
| H                    | 9.40 | 10.41 | 9.91  |
| L                    | 1.40 | 1.78  | 1.59  |
| L3                   | 0.88 | 1.27  | 1.08  |
| L4                   | 0.64 | 1.02  | 0.83  |
| a                    | 0°   | 10°   | —     |
| All Dimensions in mm |      |       |       |

## Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 11.6          |
| X1         | 1.5           |
| X2         | 7.0           |
| Y1         | 2.5           |
| Y2         | 7.0           |
| C          | 6.9           |
| E1         | 2.3           |

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